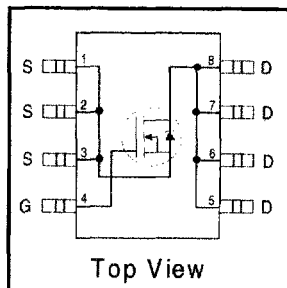


IRF7601

HEXFET® Power MOSFET

- Generation V Technology
- Ultra Low On-Resistance
- N-Channel MOSFET
- Very Small SOIC Package
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching



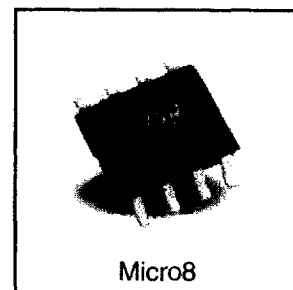
$$V_{DS} = 20V$$

$$R_{DS(on)} = 0.035\Omega$$

Description

Fifth Generation HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design for which HEXFET Power MOSFETs are well known, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The new Micro8 package, with half the footprint area of the standard SO-8, provides the smallest footprint available in an SOIC outline. This makes the Micro8 an ideal device for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro8 will allow it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5V$	5.7	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 4.5V$	4.6	
I_{DM}	Pulsed Drain Current ①	30	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	1.8	W
	Linear Derating Factor	14	mW/°C
V_{GS}	Gate-to-Source Voltage	± 12	V
dv/dt	Peak Diode Recovery dv/dt ②	5.0	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to +150	°C

Thermal Resistance

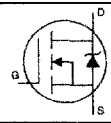
	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	—	70	°C/W

All Micro8 data sheets reflect improved thermal resistance, power, and current handling ratings (effective only for product marked with date code 505 or later.)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.024	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.035	Ω	$V_{GS} = 4.5V, I_D = 3.8A$ ③
		—	—	0.050		$V_{GS} = 2.7V, I_D = 1.9A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	0.70	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	6.1	—	—	S	$V_{DS} = 10V, I_D = 1.9A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 16V, V_{GS} = 0V$
		—	—	25		$V_{DS} = 16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -12V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 12V$
Q_g	Total Gate Charge	—	14	22	nC	$I_D = 3.8A$
Q_{gs}	Gate-to-Source Charge	—	2.0	3.0		$V_{DS} = 16V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	6.3	9.5		$V_{GS} = 4.5V$, see figure 6 and 9 ③
$t_{d(on)}$	Turn-On Delay Time	—	5.1	—	ns	$V_{DD} = 10V$
t_r	Rise Time	—	47	—		$I_D = 3.8A$
$t_{d(off)}$	Turn-Off Delay Time	—	24	—		$R_G = 6.2\Omega$
t_f	Fall Time	—	32	—		$R_D = 2.6\Omega$, see figure 10 ③
C_{iss}	Input Capacitance	—	650	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	300	—		$V_{DS} = 15V$
C_{rss}	Reverse Transfer Capacitance	—	150	—		$f = 1.0\text{MHz}$, see figure 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current	—	—	1.8	A	MOSFET symbol showing the integral reverse p-n junction diode. 
	(Body Diode)	—	—	1.8		
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	30	A	
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}, I_S = 3.8A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	51	77	ns	$T_J = 25^\circ\text{C}, I_F = 3.8A$
Q_{rr}	Reverse Recovery Charge	—	69	100	nC	$di/dt = 100A/\mu s$ ③

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (see figure 11)
- ② $I_{SD} \leq 3.8A, di/dt \leq 96A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$
- ③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ④ Surface mounted on FR-4 board, $t \leq 10$ sec.

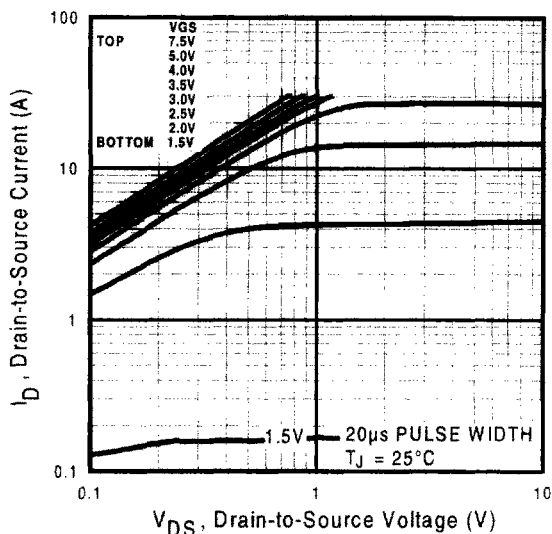


Fig 1. Typical Output Characteristics

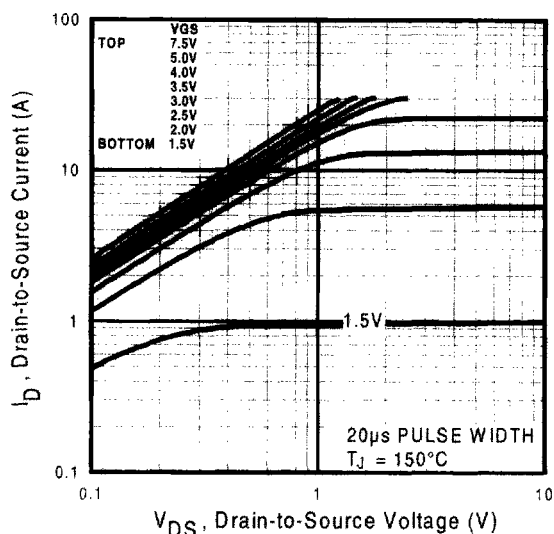


Fig 2. Typical Output Characteristics

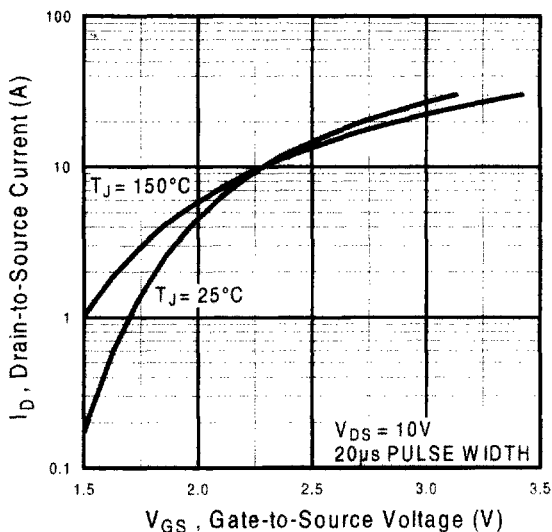


Fig 3. Typical Transfer Characteristics

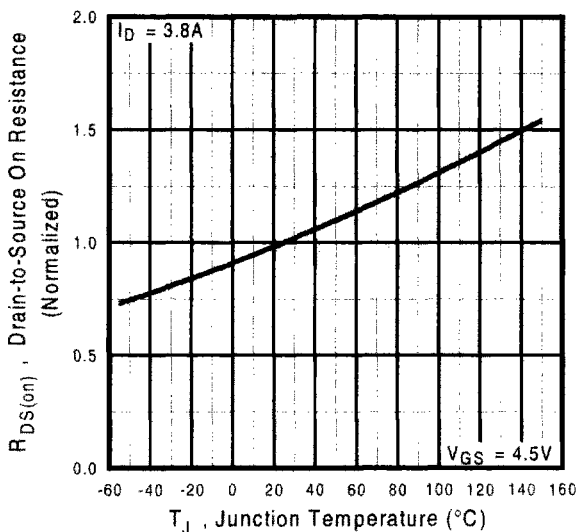


Fig 4. Normalized On-Resistance
Vs. Temperature

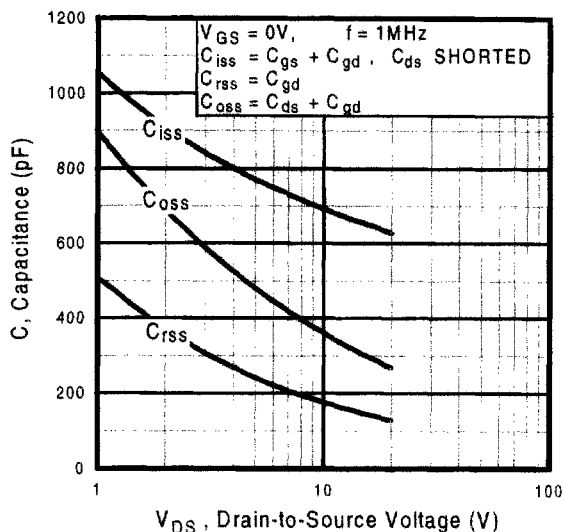


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

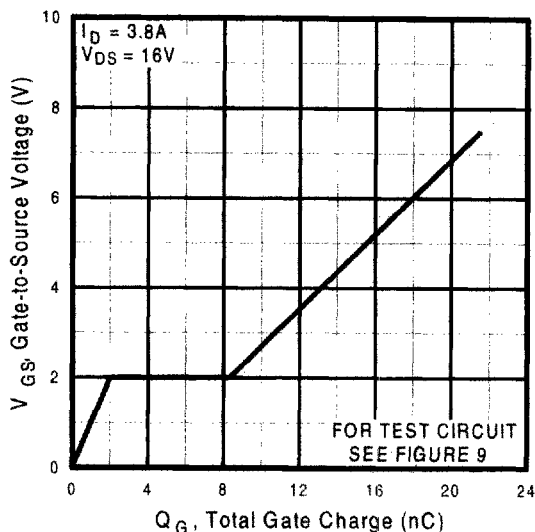


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

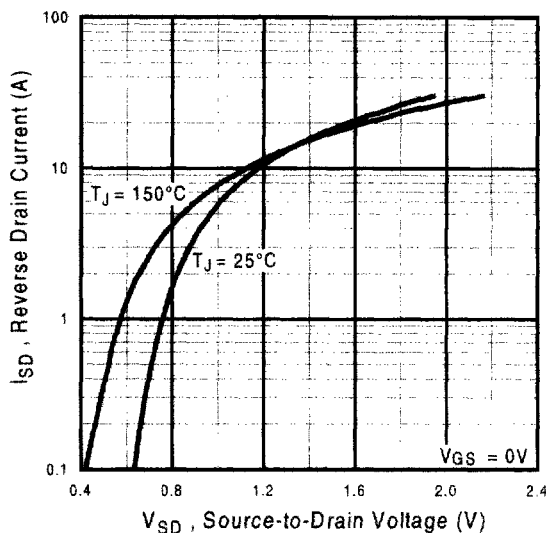


Fig 7. Typical Source-Drain Diode Forward Voltage

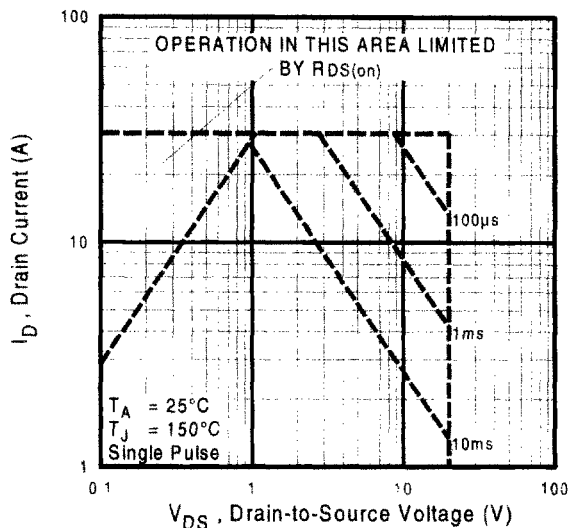


Fig 8. Maximum Safe Operating Area

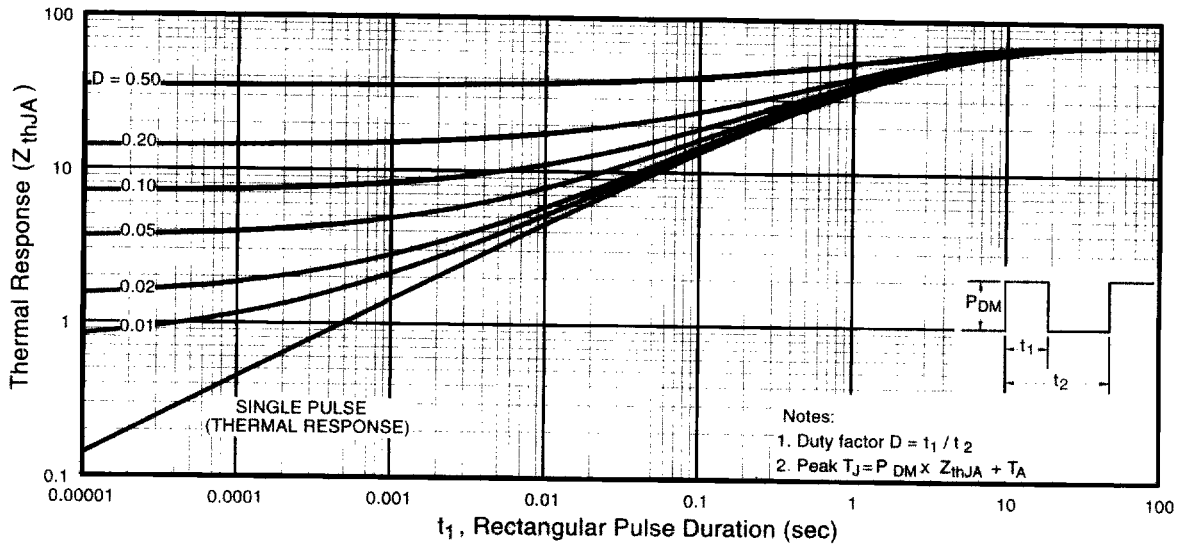


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient